SHI LING® 浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

Specifcation of products

：

：MFK200U4K2

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Symbol	Parameter	Test Conditions	Values	Unit
V_R	Maximum D.C. Reverse Voltage		400	V
V_{RRM}	Maximum Repetitive Reverse Voltage		400	V
$I_{F(AV)}$	Average Forward Current	T_C=110℃, Per Diode	100	A
		T_C=110℃, Per Moudle	200	A
$I_{F(RMS)}$	RMS Forward Current	T_C=110℃, Per Diode	150	A
I_{FSM}	Non-Repetitive Surge Forward Current	T_J=45℃, t=10ms, 50Hz, Sine	1250	A
		T_J=45℃, t=8.3ms, 60Hz, Sine	1360	A
I^2t	I^2t (For Fusing)	T_J=45℃, t=10ms, 50Hz, Sine	7800	A^2s
		T_J=45℃, t=8.3ms, 60Hz, Sine	7600	A^2s
P_D	Power Dissipation W		615	W
T_J	Junction Temperature		-40 to +150	℃

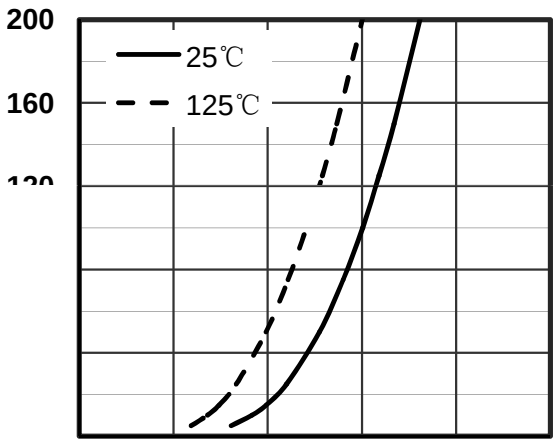


Figure 1. Forward Voltage Drop vs Forward Current

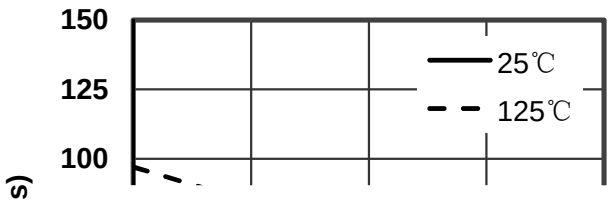
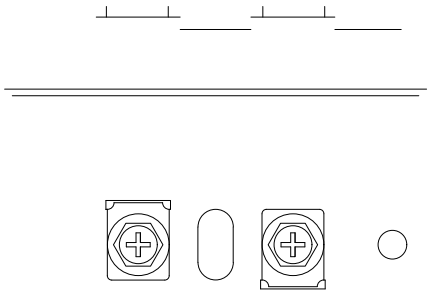
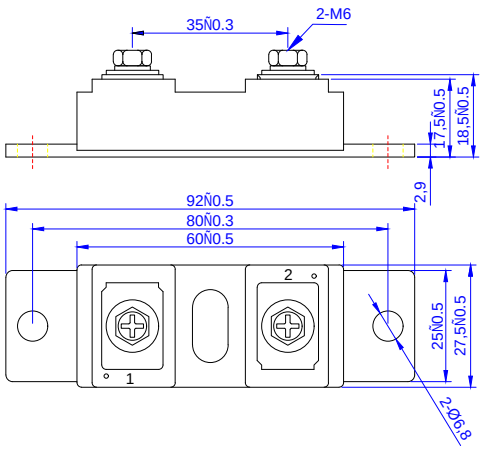


Figure 2. Reverse Recovery Time vs dI$_F$/dt




35Ñ0.3
2-M6
17,5Ñ0.5
18.5Ñ0.5
2.9
92Ñ0.5
80Ñ0.3
60Ñ0.5
2
1
25Ñ0.5
27.5Ñ0.5
2-Ø6.8